ECE321 – Electronics I

Lecture 23: Logic Design Style: Static

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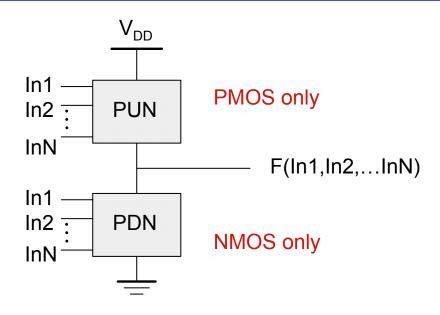
Review of Last Lecture

- **☐** Transmission Gates
 - Basic circuit for Transmission Gate
 - Circuit analysis Techniques
 - Complex Logic Gates using Pass Transistors

Today's Lecture

- ☐ CMOS Static Gates
 - Implementation of a Complex Logic
 - Circuit Analysis for CMOS Static Gates
 - Transistor Sizing

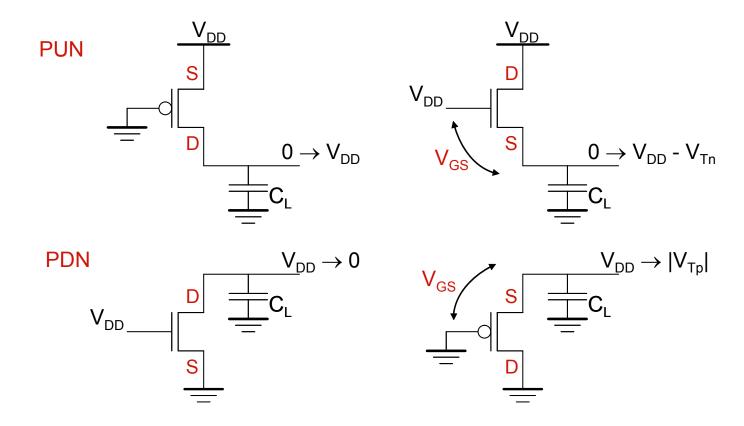
Static CMOS Logic Gate



PUN and PDN are dual logic networks

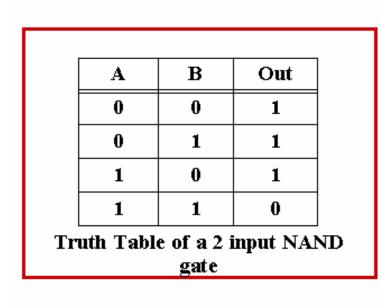
- ☐ Static Logic is a gate where the output is maintained at 0 or 1 as long as power is applied
- ☐ PUN and PDN are dual (Complimentary) to drive the output from 0 to 1 and 1 to 0 full rail (VSS to VDD)

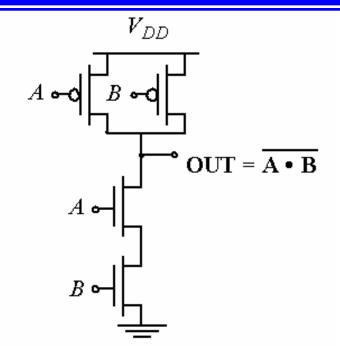
PUN and PDN Networks



- □ NMOS is a good pull down device (PDN)
- ☐ PMOS is a good pull up device (PUN)

Example: NAND Gate





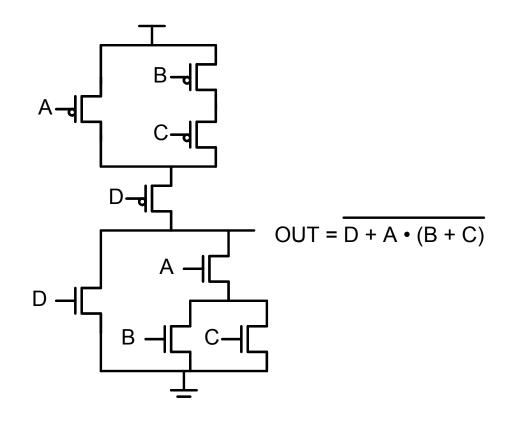
PUN: $\overline{A} + \overline{B} = \overline{AB}$ (Conduction to VDD)

PDN: AB (Conduction to GND)

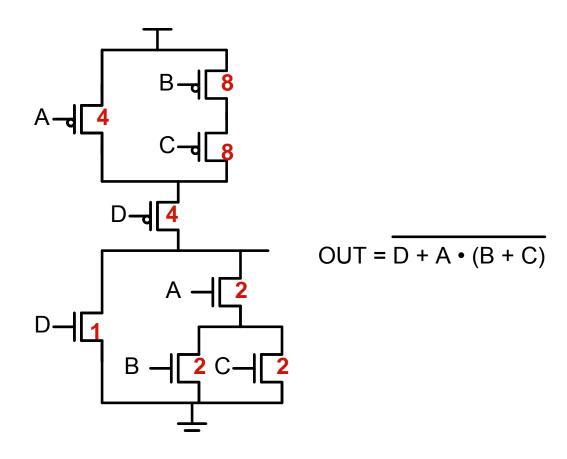
☐ How do you size transistors to have approximately the same delay as an inverter?

Example: More Complicated Gate

- □ Consider F=D+A(B+C)
 - Stacks give the AND function
 - Parallel gates give the OR function
- Derive the PDN in hierarchical fashion
- ☐ Build the complement for the PUN
 - Convert stacks to parallel
 - Convert parallel to stacks



Transistor Sizing of a Complex CMOS Gate



 Size of transistors to have the same delay of an inverter when (W/L)_P=2 and (W/L)_N=1

Circuit Analysis for Complex Gates

- ☐ To analyze complex gates for delay, power, and VTC, use the same concepts you have learned for inverter.
- **Example: A CMOS** gate with V_{DD} =5V is designed such that the base (W/L)=10. Assume that $V_{Tn}=0.7$, V_{T_0} =-0.6, K'_n =100 uA/V^2 , $K'_p = -60 uA/V^2$, and the load capacitance is 100fF. Use the constant current source model to find the best case and the worst case t_{pHL} and t_{pLH}

